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and Next-Generation  
Lithography Mask Technology***

**Hiroshi Nakata**  
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# Contents

vii *Conference Committee*

---

## OPENING SESSION DAY 1: KEYNOTE AND EUV BLANK TECHNOLOGY

- 13177 02 **Development of next generation EUV mask blanks (Invited Paper)** [13177-34]  
13177 03 **Actinic blank inspection for high-NA EUV lithography (Invited Paper)** [13177-27]

---

## FPD-RELATED AND MATURED TECHNOLOGIES

- 13177 04 **Development of phase-shift masks to meet the market demand for high resolution**  
[13177-38]  
13177 05 **Model-based compensation for thermal position drifts** [13177-30]

---

## SPECIAL SESSION: CHIPLET AND HETEROGENOUS

- 13177 06 **Solutions enabling advanced packaging and heterogeneous integration (Invited Paper)**  
[13177-22]

---

## NIL

- 13177 07 **A proof of concept for hybrid nano-imprint lithography (Invited Paper)** [13177-17]  
13177 08 **Nanoimprint performance improvements for high volume semiconductor device  
manufacturing** [13177-29]  
13177 09 **NIL solutions using computational lithography for semiconductor device manufacturing**  
[13177-19]

---

## COMPUTATIONAL SOLUTIONS FOR WRITING/METROLOGY

- 13177 0A **12th eBeam initiative survey reports semiconductor industry luminaries are confident in  
high-NA EUV and curvilinear photomasks (Invited Paper)** [13177-5]  
13177 0B **Integration of E-beam mask writer corrections in MPC applications (Invited Paper)**  
[13177-31]  
13177 0C **Curvilinear mask metrology: What's the 2D equivalent of CD?** [13177-26]

---

#### LITHOGRAPHY-RELATED TECHNOLOGIES

---

- 13177 0D **Rethinking mask strategies for high vertical resolution grayscale lithography** [13177-7]
- 13177 0E **Applicability of projection exposure using a gradient-index lens array to thick resist patterning of more than 100- $\mu\text{m}$**  [13177-2]

---

#### OPENING SESSION DAY 2: KEYNOTE AND STITCHING

---

- 13177 0F **High NA EUV stitching: mask performance is a key (Invited Paper)** [13177-36]
- 13177 0G **Exploring high-NA EUV mask specification for logic metal** [13177-43]
- 13177 0H **Throughput simulations of the two-mask stage for high-NA EUV scanners** [13177-4]

---

#### MASK PROCESS TECHNOLOGIES

---

- 13177 0I **Evaluation and countermeasures verification of haze on ArF PSM** [13177-41]
- 13177 0J **A study of CrOx composed progressive defect on attenuated PSM and its damaged-free removal process** [13177-24]
- 13177 0K **A study on directional damaged defect in photomask manufacturing process** [13177-20]

---

#### ENERGY SUSTAINABILITY IN LITHOGRAPHY

---

- 13177 0L **Research and development of the EUV-FEL light source for lithography** [13177-28]
- 13177 0M **Can we improve the energy efficiency of EUV lithography?** [13177-42]

---

#### OPENING SESSION DAY 3: EUV PROCESS TECHNOLOGIES

---

- 13177 0N **Readiness for predictive maintenance of high cost EUV equipment using big data** [13177-10]
- 13177 0O **Imaging evaluation of low reflectivity low-n EUV mask for LS at 0.33NA** [13177-15]

---

#### ACTINIC INSPECTION

---

- 13177 0P **EUV mask inspection technologies with actinic tool for DRAM and logic lithography** [13177-3]
- 13177 0Q **Actinic inspection improvement and application in high volume manufacturing for N3 node and beyond** [13177-6]

---

**REPAIR AND METROLOGY**

---

- 13177 OR **AFM nanomachining and clean repair of EUV TaBN and high-k advanced absorber materials** [13177-8]
- 13177 OS **Application of advanced laser repair to legacy photomasks** [13177-9]

---

**WRITING TOOLS AND PATTERNING TECHNOLOGIES**

---

- 13177 OT **Make a core engine ready to empower high quality multi-beam mask writer for N2 node and beyond** [13177-21]
- 13177 OU **Recent advancements of multibeam mask writer MBM-3000** [13177-37]
- 13177 OV **Improvement of mask pattern placement error using novel resist charging control methodology in multi-beam mask writer** [13177-11]

---

**POSTER SESSION**

---

- 13177 OW **Improvement of critical dimension uniformity using machine learning** [13177-25]
- 13177 OX **Enhancement of mask data verification with Smart-MRC and machine learning** [13177-33]
- 13177 OY **Projection exposure on inner surfaces of cylindrical pipes using a cone mirror** [13177-13]
- 13177 OZ **Projection lithography using 125- $\mu\text{m}$  square optical fibers and an LED matrix** [13177-18]
- 13177 10 **Local registration (LREG) measurement for beam deflector monitoring** [13177-23]
- 13177 11 **Beyond EUV binary and phase shift masks simulation** [13177-35]
- 13177 12 **Deposition of high-density carbon layer for beyond EUV lithography** [13177-40]
- 13177 13 **Mo/Si multilayer improvements for EUV photomask performance** [13177-39]
- 13177 14 **A short wavelength light source for lithography using a regenerative liquid metal bismuth target** [13177-16]
- 13177 15 **Spatial separation of EUV emission and energetic ions by use of double-laser-pulse irradiation** [13177-14]